

# QORVO

## SiC JFET Division

### Is Now Part of

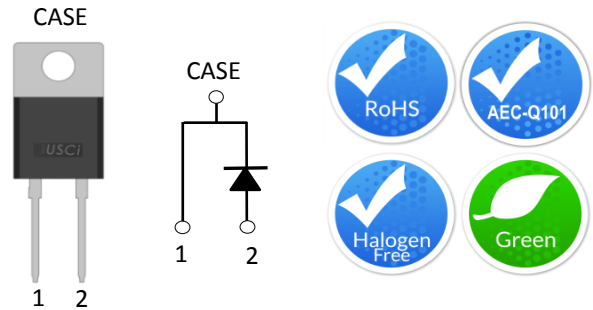
# onsemi™

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## Description

United Silicon Carbide, Inc. offers the 3<sup>rd</sup> generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



## Features

- ◆ 175°C maximum operating junction temperature
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ 100% UIS tested
- ◆ AEC-Q101 qualified
- ◆ AECQ Qualified

Part Number	Package	Marking
UJ3D06520TS	TO-220-2L	UJ3D06520TS

## Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

## Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	$V_R$		650	V
Repetitive peak reverse voltage, $T_j=25^\circ\text{C}$	$V_{RRM}$		650	V
Surge peak reverse voltage	$V_{RSM}$		650	V
Maximum DC forward current	$I_F$	$T_C = 152^\circ\text{C}$	20	A
Non-repetitive forward surge current sine halfwave	$I_{FSM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	126	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	108	
Repetitive forward surge current sine halfwave, $D=0.1$	$I_{FRM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	83	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	52	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	820	A
		$T_C = 110^\circ\text{C}, t_p = 10\mu\text{s}$	820	
$i^2t$ value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	79.4	$\text{A}^2\text{s}$
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	58.3	
Power dissipation	$P_{Tot}$	$T_C = 25^\circ\text{C}$	272.7	W
		$T_C = 152^\circ\text{C}$	41.8	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	$T_J, T_{STG}$		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	$T_{sold}$	1.6mm from case for 10s	260	$^\circ\text{C}$

### Electrical Characteristics

$T_J = +25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	$V_F$	$I_F = 20\text{A}, T_J = 25^\circ\text{C}$	-	1.5	1.7	V
		$I_F = 20\text{A}, T_J = 150^\circ\text{C}$	-	1.68	2.0	
		$I_F = 20\text{A}, T_J = 175^\circ\text{C}$	-	1.75	2.1	
Reverse current	$I_R$	$V_R = 650\text{V}, T_J = 25^\circ\text{C}$	-	20	120	$\mu\text{A}$
		$V_R = 650\text{V}, T_J = 175^\circ\text{C}$	-	300		
Total capacitive charge <sup>(1)</sup>	$Q_C$	$V_R = 400\text{V}$		46		nC
Total capacitance	C	$V_R = 1\text{V}, f = 1\text{MHz}$		654		pF
		$V_R = 300\text{V}, f = 1\text{MHz}$		76		
		$V_R = 600\text{V}, f = 1\text{MHz}$		68		
Capacitance stored energy	$E_C$	$V_R = 400\text{V}$		6.8		$\mu\text{J}$

(1)  $Q_C$  is independent on  $T_J$ ,  $di_F/dt$ , and  $I_F$  as shown in the application note USCi\_AN0011.

### Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction - case	$R_{\theta JC}$			0.41	0.55	$^\circ\text{C/W}$

### Typical Performance

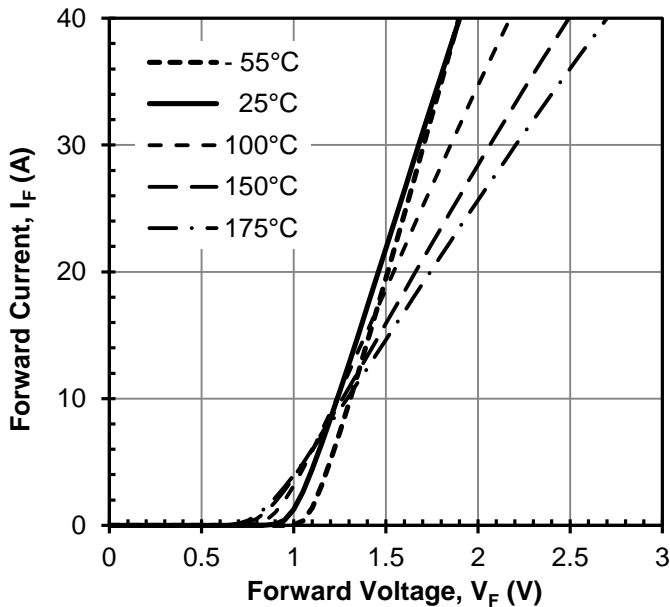


Figure 1 Typical forward characteristics

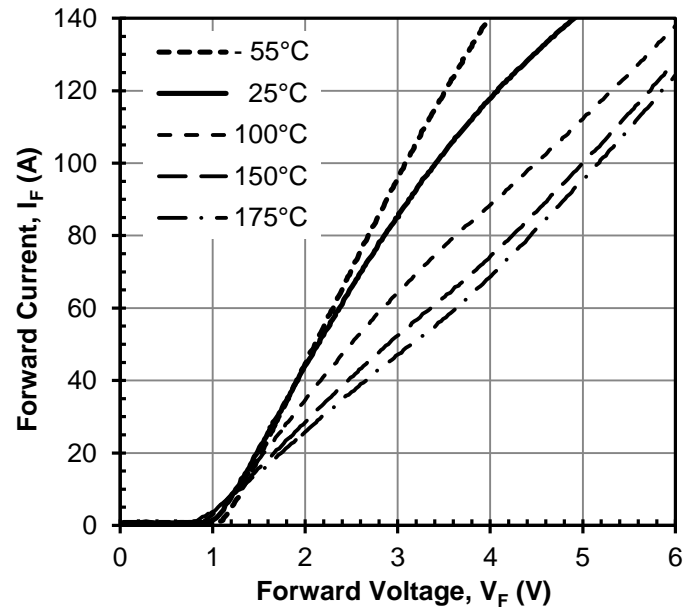


Figure 2 Typical forward characteristics in surge current

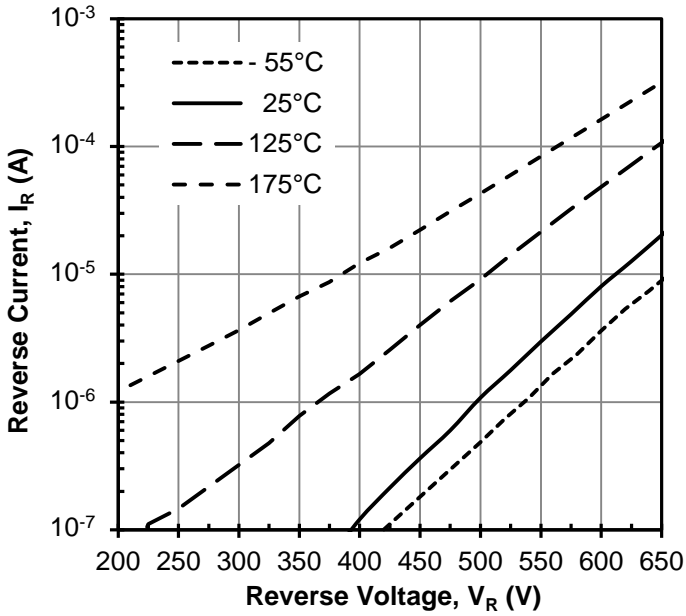


Figure 3 Typical reverse characteristics

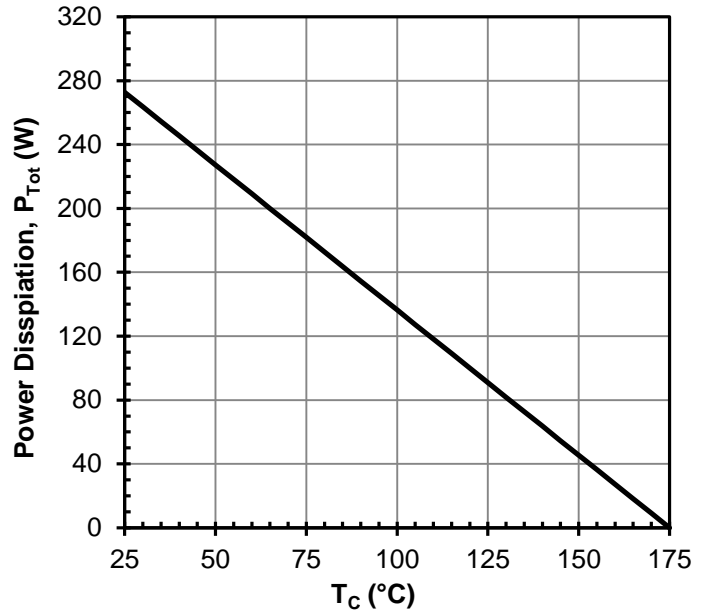


Figure 4 Power dissipation

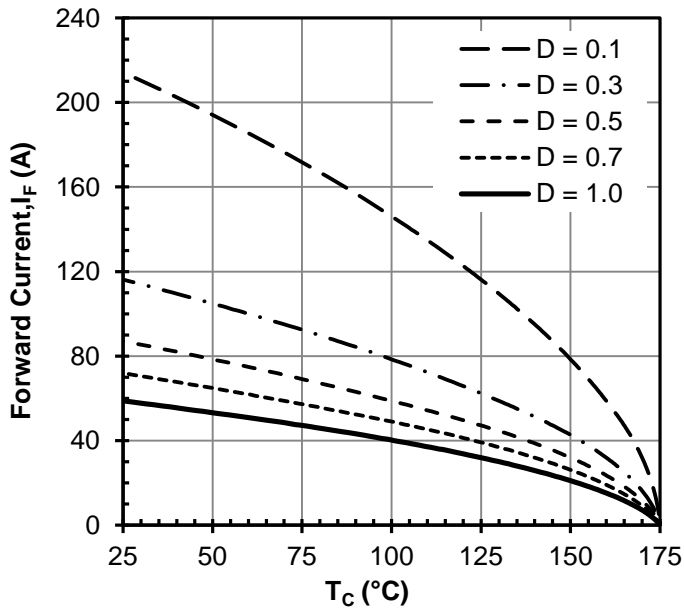


Figure 5 Diode forward current

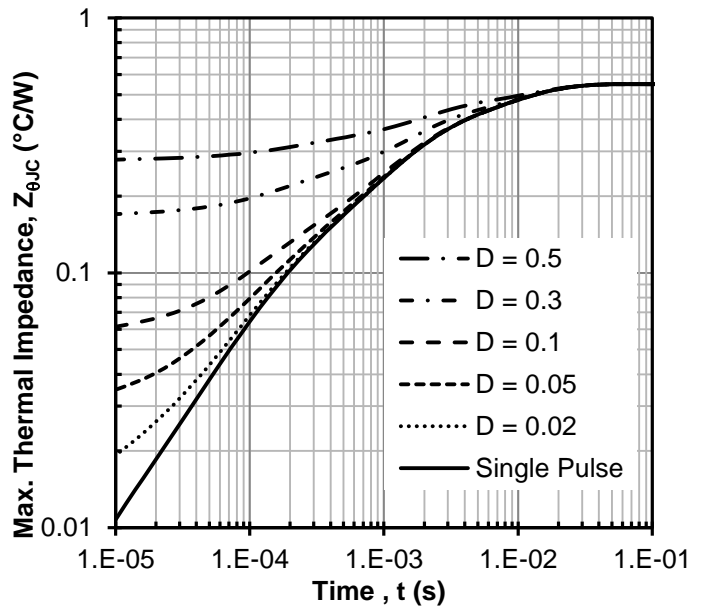
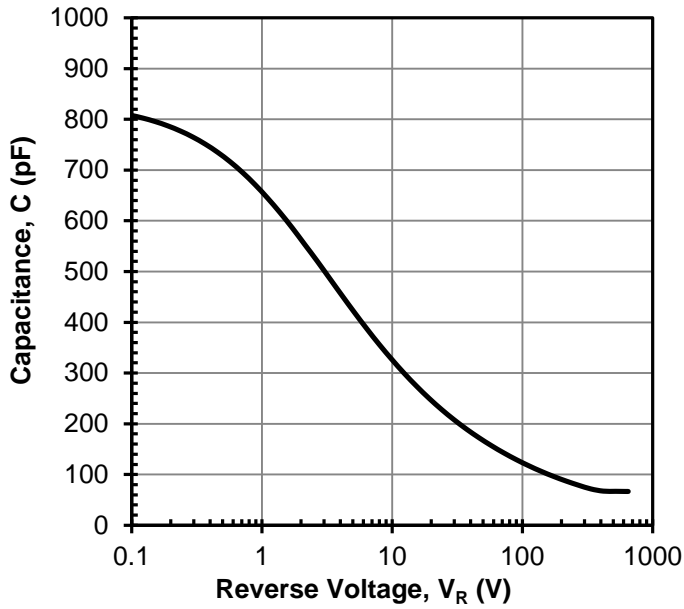
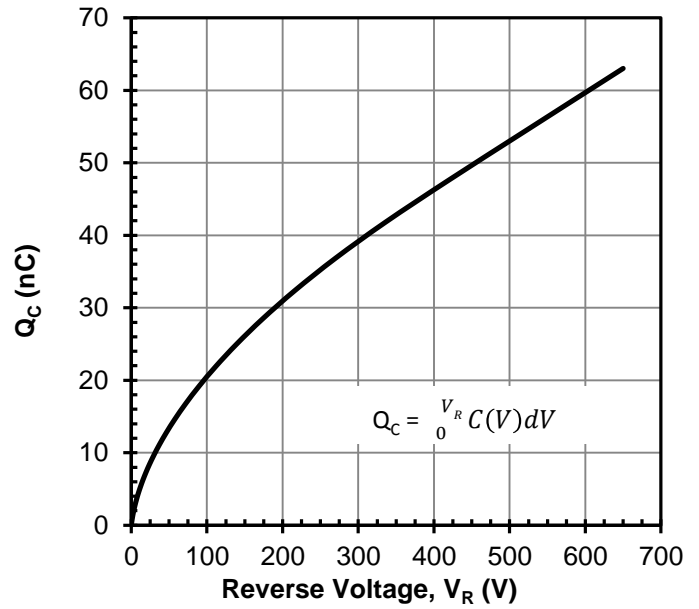


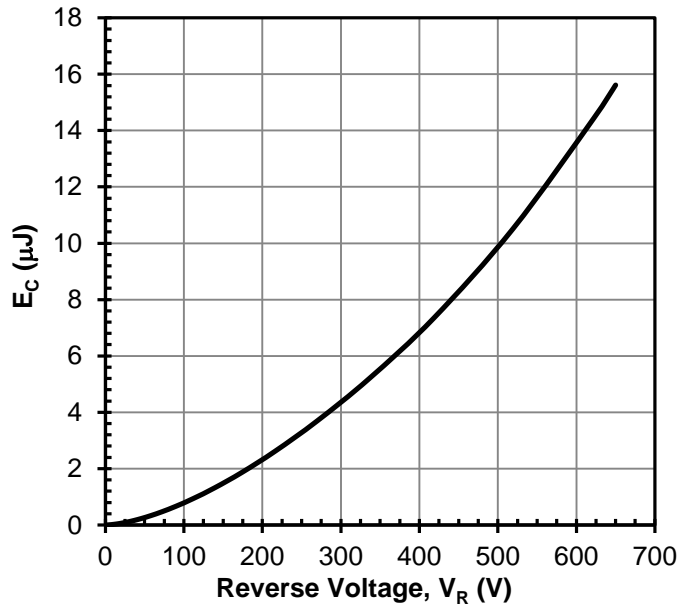
Figure 6 Maximum transient thermal impedance



**Figure 7** Capacitance vs. reverse voltage at 1MHz



**Figure 8** Typical capacitive charge vs. reverse voltage



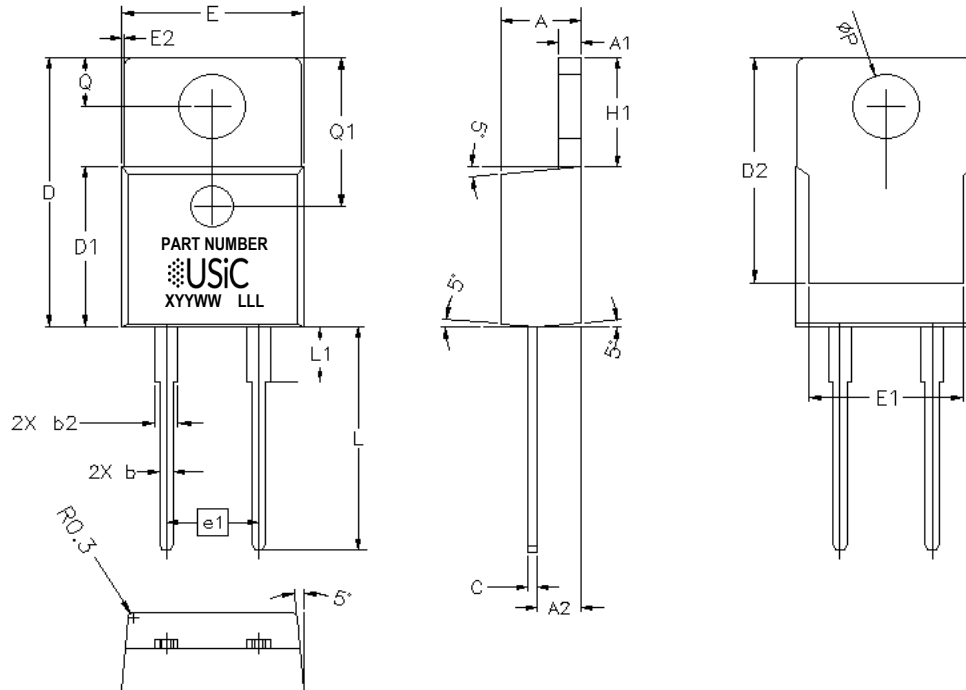
**Figure 9** Typical capacitance stored energy vs. reverse voltage

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**PACKAGE OUTLINE**


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.140	0.190	3.56	4.83
A1	0.020	0.055	0.51	1.40
A2	0.080	0.115	2.03	2.92
b	0.015	0.040	0.38	1.02
b2	0.040	0.070	1.02	1.78
C	0.014	0.030	0.36	0.76
D	0.560	0.650	14.22	16.51
D1	0.330	0.370	8.38	9.40
D2	0.480	0.517	12.19	13.13
E	0.380	0.420	9.65	10.67
e1	0.200 BSC		5.08 BSC	
E1	0.270	0.350	6.86	8.89
E2	-	0.030		0.76
L	0.495	0.580	12.57	14.73
L1	-	0.250	-	6.35
ØP	0.139	0.161	3.53	4.09
H	0.230	0.270	5.84	6.86
Q	0.100	0.135	2.54	3.43
Q1	0.330	0.340	8.38	8.64

**PART MARKING**

**PART NUMBER**  
  
**XYYWW LLL**

PART NUMBER = REFER TO  
DS\_PN DECODER FOR DETAILS

X = ASSEMBLY SITE

YY = YEAR

WW = WORK WEEK

LLL = LOT ID

**PACKING TYPE**

ANTI-STATIC TUBE

QUANTITY /TUBE : 50 UNITS

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